

Product Summary

Device	V _{(BR)DSS}	R _{D(S)} max	I _D max T _A = +25°C
Q1	30V	1.5Ω @ V _{GS} = 4.5V	0.22A
		2.0Ω @ V _{GS} = 2.5V	
		3.0Ω @ V _{GS} = 1.8V	
		4.5Ω @ V _{GS} = 1.5V	
Q2	-30V	5Ω @ V _{GS} = -4.5V	-0.2A
		6Ω @ V _{GS} = -2.5V	
		7Ω @ V _{GS} = -1.8V	
		10Ω @ V _{GS} = -1.5V	

Description

This MOSFET has been designed to minimize the on-state resistance (R_{D(S)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

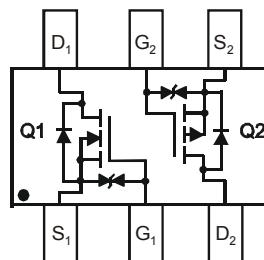
- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch



Top View



Top View

Top View
Schematic and
Transistor Diagram

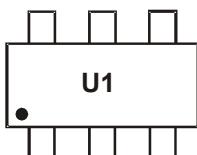
Ordering Information (Note 4)

Part Number	Case	Packaging
DMC31D5UDJ-7	SOT963	10K/Tape & Reel
DMC31D5UDJ-7B	SOT963	10K/Tape & Reel

Notes:

- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- For packaging details, go to our website at <http://www.diodes.com/products/packages.html>. The options -7 and -7B stand for different taping orientations.

Marking Information



U1 = Product Type Marking Code

Maximum Ratings Q1 N-CHANNEL (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	30	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 5) $V_{GS} = 4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	220 160	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	200	mA
Pulsed Drain Current (Note 6)			I_{DM}	600	mA

 Maximum Ratings Q2 P-CHANNEL (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	± 12	V
Continuous Drain Current (Note 5) $V_{GS} = -4.5\text{V}$	Steady State	$T_A = +25^\circ\text{C}$ $T_A = +70^\circ\text{C}$	I_D	-200 -140	mA
Maximum Continuous Body Diode Forward Current (Note 6)			I_S	-200	mA
Pulsed Drain Current (Note 6)			I_{DM}	-600	mA

 Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		P_D	350	mW
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	361	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

 Electrical Characteristics Q1 N-CHANNEL (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV_{DSS}	30	—	—	V	$V_{GS} = 0\text{V}, I_D = 250\mu\text{A}$
Zero Gate Voltage Drain Current @ $T_C = +25^\circ\text{C}$	$I_{DS(0)}$	—	—	100	nA	$V_{DS} = 24\text{V}, V_{GS} = 0\text{V}$
Gate-Source Leakage	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 10\text{V}, V_{DS} = 0\text{V}$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	$V_{GS(th)}$	0.4	—	1.0	V	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	0.9	1.5	Ω	$V_{GS} = 4.5\text{V}, I_D = 100\text{mA}$
		—	1.0	2.0		$V_{GS} = 2.5\text{V}, I_D = 50\text{mA}$
		—	1.2	3.0		$V_{GS} = 1.8\text{V}, I_D = 20\text{mA}$
		—	1.4	4.5		$V_{GS} = 1.5\text{V}, I_D = 10\text{mA}$
		—	2.3	—		$V_{GS} = 1.2\text{V}, I_D = 1\text{mA}$
Diode Forward Voltage	V_{SD}	—	0.6	1.0	V	$V_{GS} = 0\text{V}, I_S = 10\text{mA}$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C_{iss}	—	22.6	—	pF	$V_{DS} = 15\text{V}, V_{GS} = 0\text{V}, f = 1.0\text{MHz}$
Output Capacitance	C_{oss}	—	2.68	—	pF	
Reverse Transfer Capacitance	C_{rss}	—	1.8	—	pF	
Total Gate Charge	Q_g	—	0.38	—	nC	$V_{GS} = 4.5\text{V}, V_{DS} = 15\text{V}, I_D = 200\text{mA}$
Gate-Source Charge	Q_{gs}	—	0.05	—	nC	
Gate-Drain Charge	Q_{gd}	—	0.07	—	nC	
Turn-On Delay Time	$t_{D(on)}$	—	3.2	—	ns	$V_{DD} = 15\text{V}, V_{GS} = 4.5\text{V}, R_G = 2\Omega, I_D = 200\text{mA}$
Turn-On Rise Time	t_r	—	2.2	—	ns	
Turn-Off Delay Time	$t_{D(off)}$	—	21	—	ns	
Turn-Off Fall Time	t_f	—	7.5	—	ns	

Electrical Characteristics Q2 P-CHANNEL (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250µA
Zero Gate Voltage Drain Current @T _C = +25°C	I _{DSS}	—	—	100	nA	V _{DS} = -24V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	µA	V _{GS} = ±10V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	—	-1.0	V	V _{DS} = V _{GS} , I _D = -250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	2.0	5	Ω	V _{GS} = -4.5V, I _D = -100mA
		—	2.5	6		V _{GS} = -2.5V, I _D = -50mA
		—	3.0	7		V _{GS} = -1.8V, I _D = -20mA
		—	3.4	10		V _{GS} = -1.5V, I _D = -10mA
		—	5.1	—		V _{GS} = -1.2V, I _D = -1mA
Diode Forward Voltage	V _{SD}	—	-0.6	-1.0	V	V _{GS} = 0V, I _S = -10mA
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	21.8	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	2.82	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	1.66	—	pF	
Total Gate Charge	Q _g	—	0.35	—	nC	V _{GS} = -4.5V, V _{DS} = -15V, I _D = -200mA
Gate-Source Charge	Q _{gs}	—	0.05	—	nC	
Gate-Drain Charge	Q _{gd}	—	0.10	—	nC	
Turn-On Delay Time	t _{D(on)}	—	3.5	—	ns	
Turn-On Rise Time	t _r	—	5.2	—	ns	V _{DD} = -15V, V _{GS} = -4.5V, R _G = 2Ω, I _D = -200mA
Turn-Off Delay Time	t _{D(off)}	—	18.8	—	ns	
Turn-Off Fall Time	t _f	—	8.7	—	ns	

Notes:

5. Device mounted on FR-4 PCB, with minimum recommended pad layout.
6. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.

N-CHANNEL

NEW PRODUCT

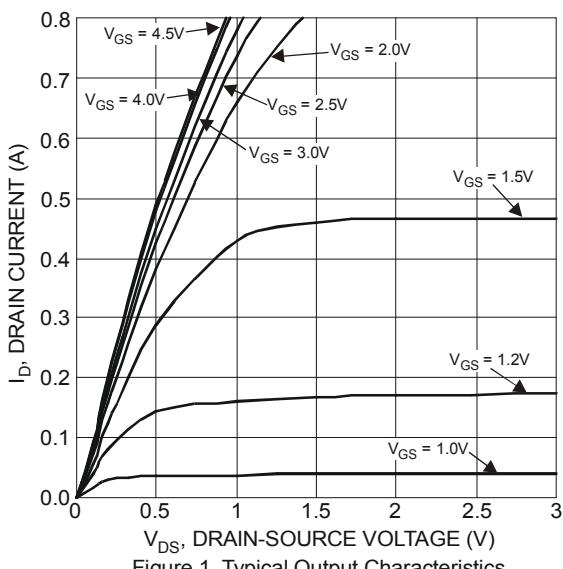


Figure 1 Typical Output Characteristics

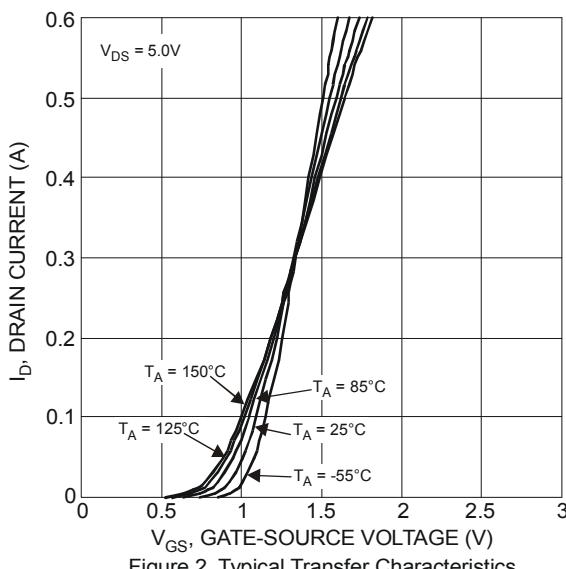


Figure 2 Typical Transfer Characteristics

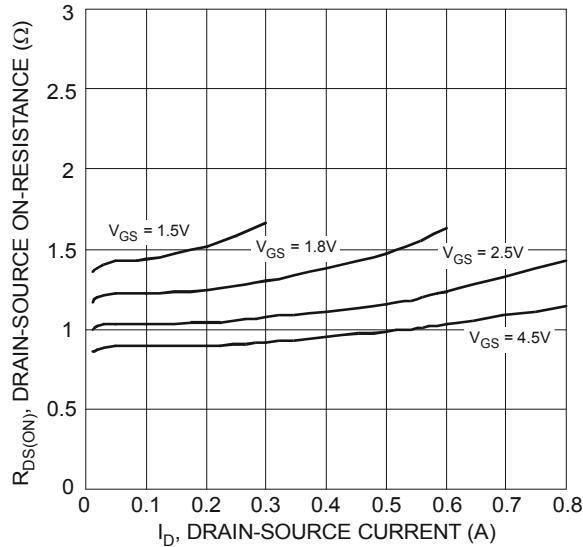


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

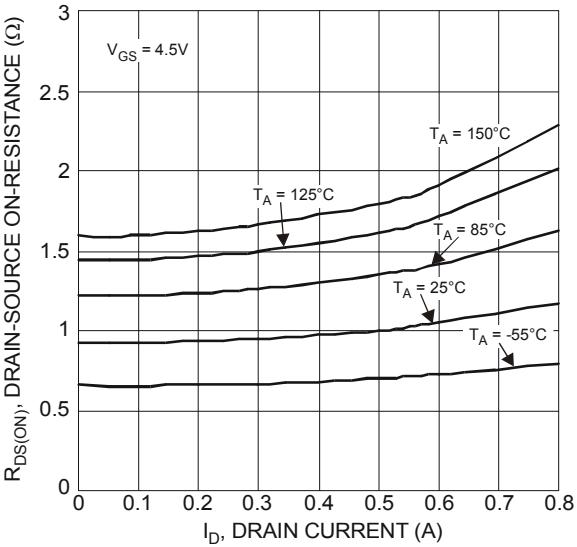


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

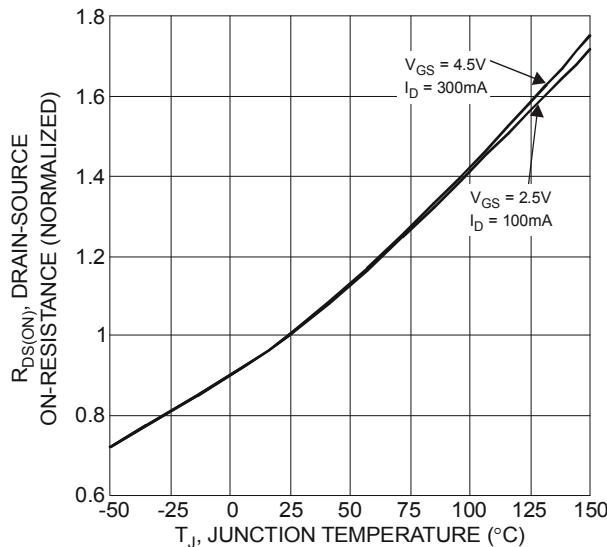


Figure 5 On-Resistance Variation with Temperature

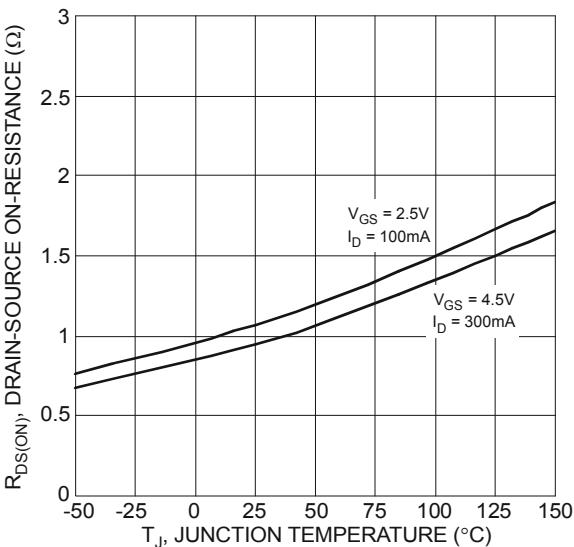


Figure 6 On-Resistance Variation with Temperature

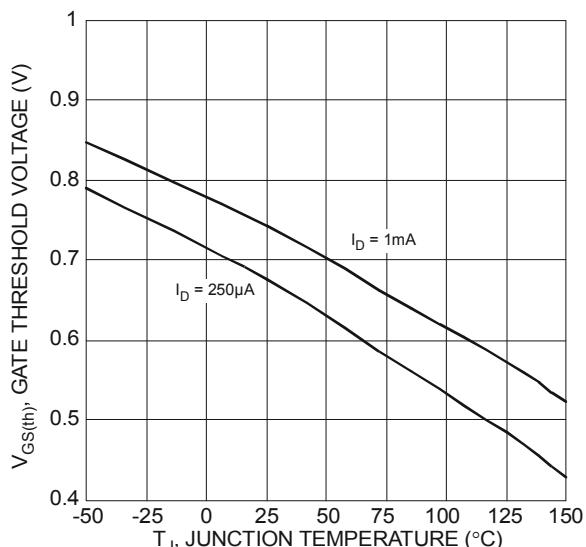


Figure 7 Gate Threshold Variation vs. Ambient Temperature

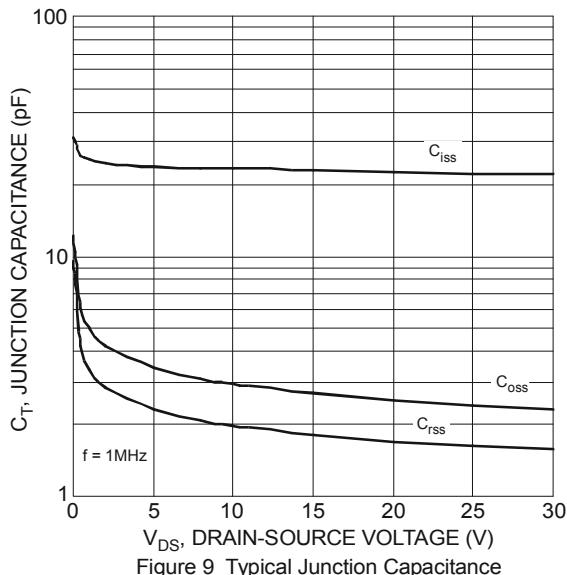


Figure 9 Typical Junction Capacitance

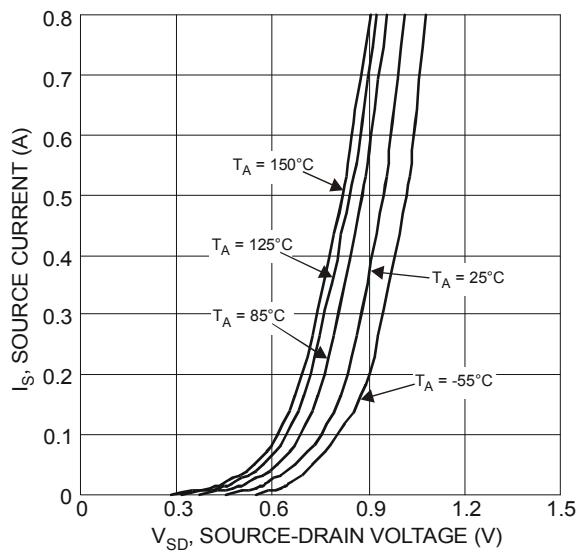


Figure 8 Diode Forward Voltage vs. Current

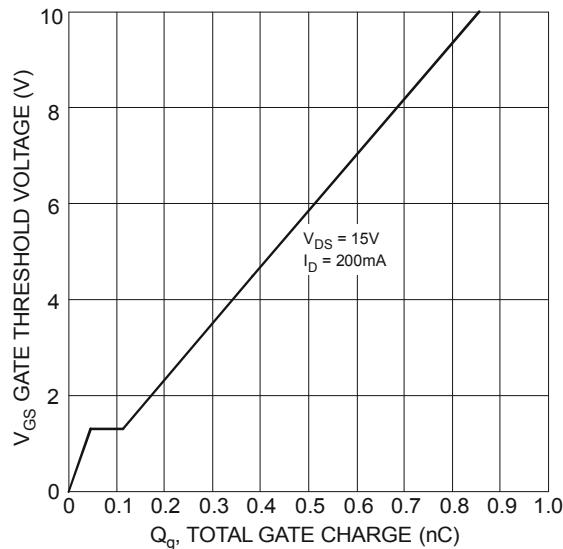


Figure 10 Gate Charge

P-CHANNEL

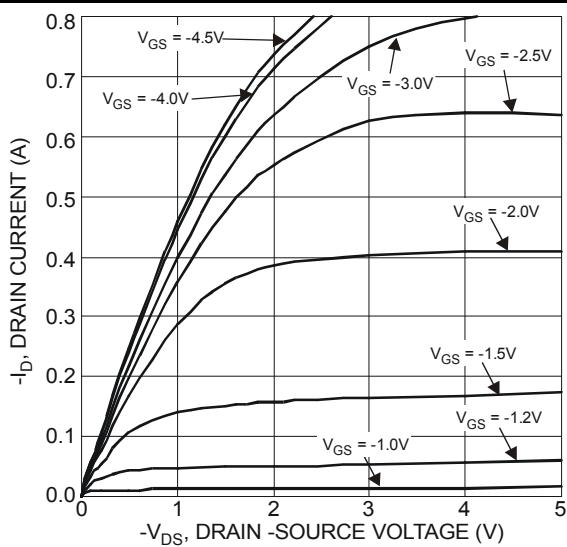


Figure 1 Typical Output Characteristics

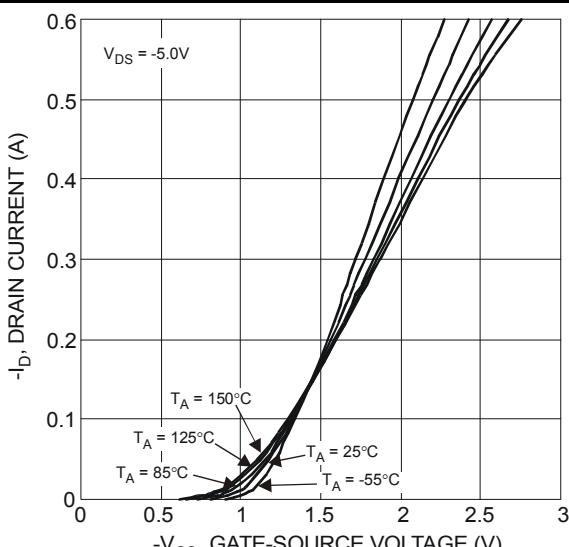


Figure 2 Typical Transfer Characteristics

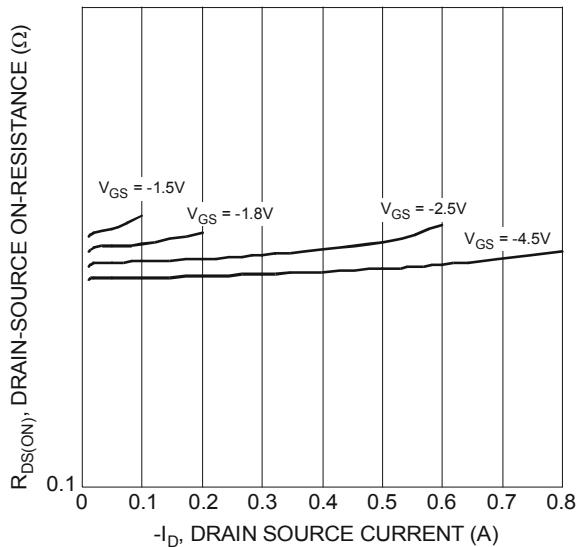


Figure 3 Typical On-Resistance vs.
Drain Current and Gate Voltage

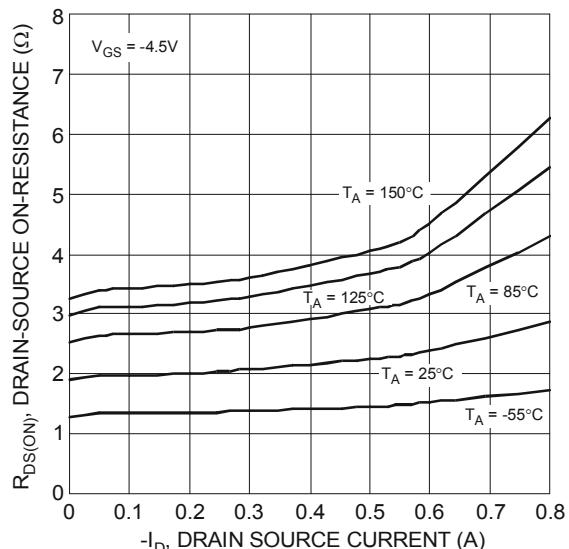


Figure 4 Typical On-Resistance vs.
Drain Current and Temperature

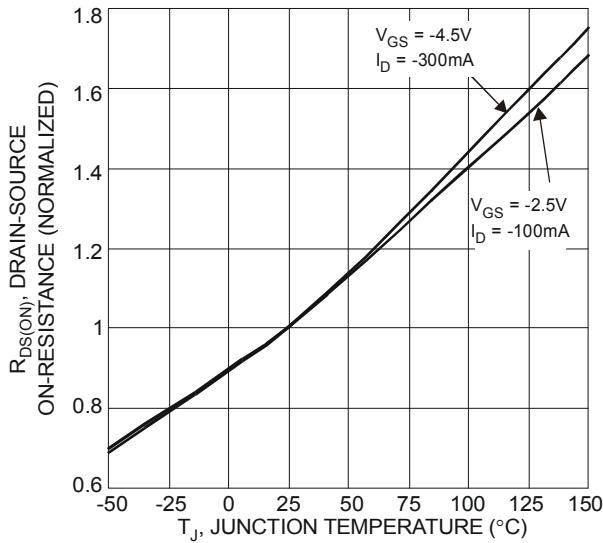


Figure 5 On-Resistance Variation with Temperature

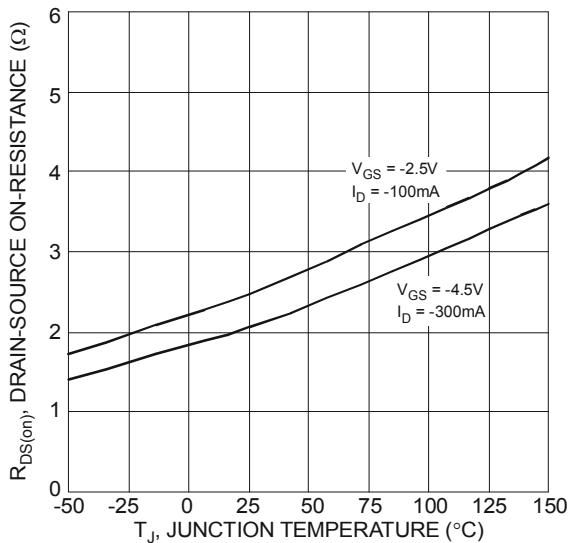


Figure 6 On-Resistance Variation with Temperature

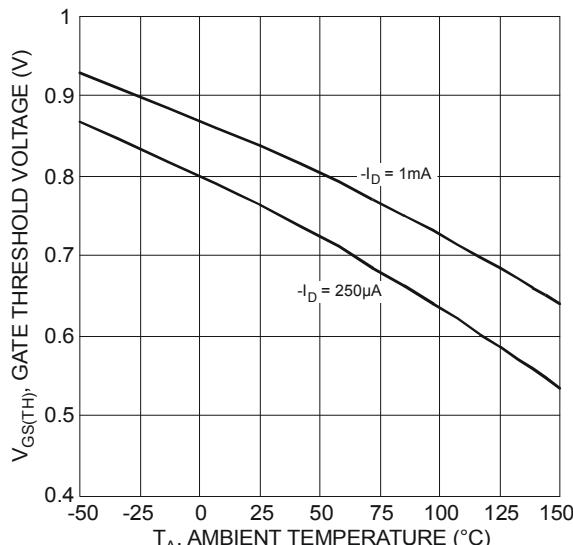


Figure 7 Gate Threshold Variation vs. Ambient Temperature

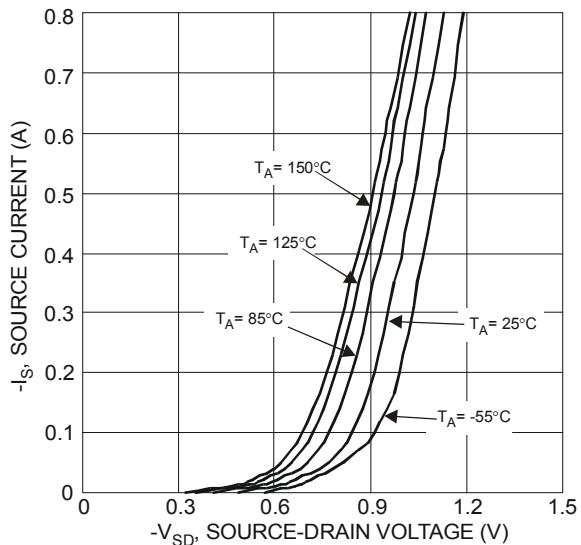


Figure 8 Diode Forward Voltage vs. Current

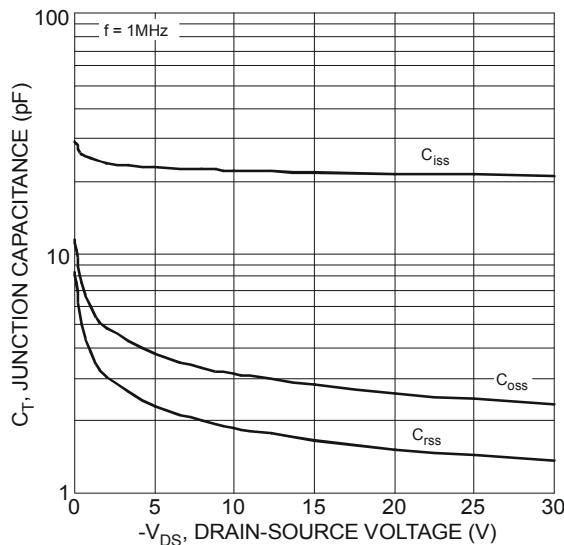


Figure 9 Typical Junction Capacitance

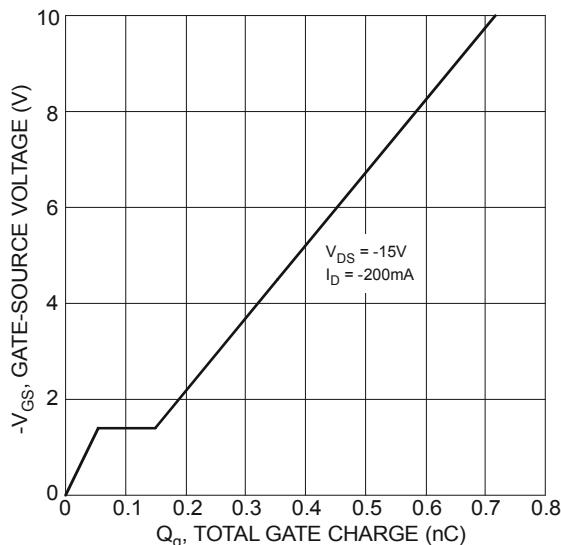


Figure 10 Gate-Charge Characteristics

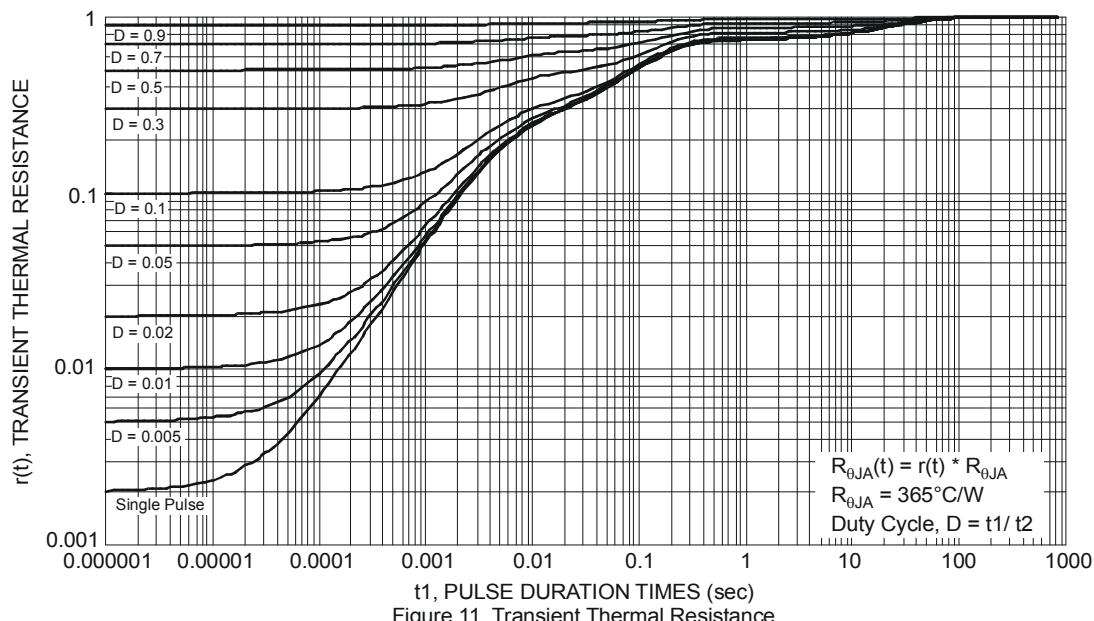
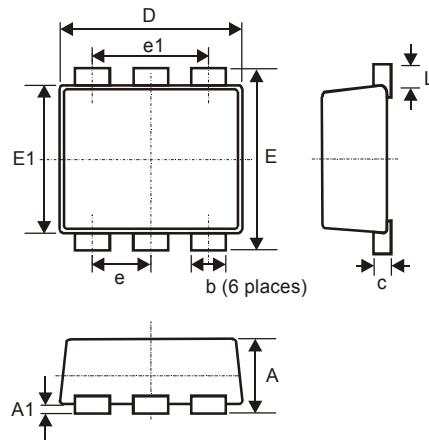


Figure 11 Transient Thermal Resistance

Package Outline Dimensions

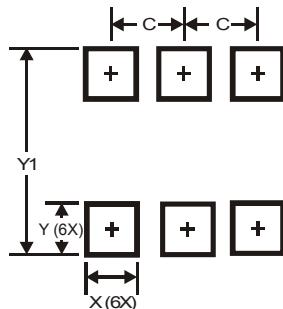
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



SOT963			
Dim	Min	Max	Typ
A	0.40	0.50	0.45
A1	0	0.05	-
c	0.120	0.180	0.150
D	0.95	1.05	1.00
E	0.95	1.05	1.00
E1	0.75	0.85	0.80
L	0.05	0.15	0.10
b	0.10	0.20	0.15
e	0.35 Typ		
e1	0.70 Typ		
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
C	0.350
X	0.200
Y	0.200
Y1	1.100

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